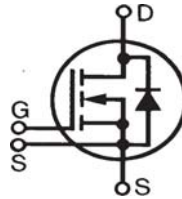


Linear™ Power MOSFET w/ Extended FBSOA

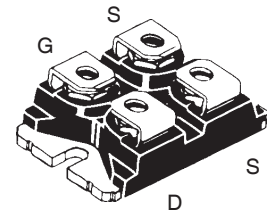
IXTN22N100L

$V_{DSS} = 1000V$
 $I_{D25} = 22A$
 $R_{DS(on)} \leq 600m\Omega$

N-Channel Enhancement Mode
Avalanche Rated



miniBLOC
E153432



G = Gate D = Drain
S = Source

Either Source Terminal S can be used as the Source Terminal or the Kelvin Source (Gate Return) Terminal.

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ C$ to $150^\circ C$	1000	V
V_{DGR}	$T_J = 25^\circ C$ to $150^\circ C$, $R_{GS} = 1M\Omega$	1000	V
V_{GSS}	Continuous	± 30	V
V_{GSM}	Transient	± 40	V
I_{D25}	$T_C = 25^\circ C$	22	A
I_{DM}	$T_C = 25^\circ C$, Pulse Width Limited by T_{JM}	50	A
I_A	$T_C = 25^\circ C$	22	A
E_{AS}	$T_C = 25^\circ C$	1.5	J
P_D	$T_C = 25^\circ C$	700	W
T_J		-55 ... +150	$^\circ C$
T_{JM}		150	$^\circ C$
T_{stg}		-55 ... +150	$^\circ C$
T_L	1.6mm (0.062 in.) from Case for 10s	300	$^\circ C$
T_{SOLD}	Plastic Body for 10s	260	$^\circ C$
V_{ISOL}	50/60 Hz, RMS $t = 1$ Minute	2500	V~
	$I_{ISOL} \leq 1mA$ $t = 1$ Second	3000	V~
M_d	Mounting Torque	1.5/13	Nm/lb.in.
	Terminal Connection Torque	1.3/11.5	Nm/lb.in.
Weight		30	g

Features

- MiniBLOC with Aluminium Nitride Isolation
- Designed for Linear Operation
- International Standard Package
- Avalanche Rated
- Molding Epoxy Meets UL94 V-0 Flammability Classification

Advantages

- Easy to Mount
- Space Savings
- High Power Density

Applications

- Programmable Loads
- Current Regulators
- DC-DC Converters
- Battery Chargers
- DC Choppers
- Temperature and Lighting Controls

Symbol	Test Conditions ($T_J = 25^\circ C$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{DSS}	$V_{GS} = 0V$, $I_D = 1mA$	1000		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	3.0		5.5 V
I_{GSS}	$V_{GS} = \pm 30V$, $V_{DS} = 0V$			± 200 nA
I_{DSS}	$V_{DS} = V_{DSS}$, $V_{GS} = 0V$ $T_J = 125^\circ C$			50 μA 1 mA
$R_{DS(on)}$	$V_{GS} = 20V$, $I_D = 0.5 \cdot I_{DSS}$, Note 1			600 m Ω

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values			
		Min.	Typ.	Max.	
g_{fs}	$V_{DS} = 20\text{V}$, $I_D = 0.5 \cdot I_{DSS}$, Note 1	4.5	7.0	9.5	S
C_{iss}	$V_{GS} = 0\text{V}$, $V_{DS} = 25\text{V}$, $f = 1\text{MHz}$		7050		pF
C_{oss}			600		pF
C_{rss}			100		pF
$t_{d(on)}$	Resistive Switching Times $V_{GS} = 15\text{V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 0.5 \cdot I_{DSS}$ $R_G = 2\Omega$ (External)		36		ns
t_r			35		ns
$t_{d(off)}$			80		ns
t_f			50		ns
$Q_{g(on)}$	$V_{GS} = 15\text{V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 0.5 \cdot I_{DSS}$		270		nC
Q_{gs}			70		nC
Q_{gd}			110		nC
R_{thJC}				0.18	$^\circ\text{C/W}$
R_{thCS}		0.05			$^\circ\text{C/W}$

Safe-Operating-Area Specification

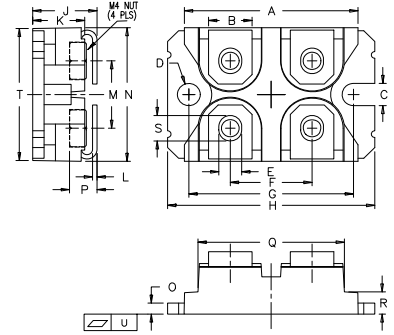
Symbol	Test Conditions	Characteristic Values			
		Min.	Typ.	Max.	
SOA	$V_{DS} = 800\text{V}$, $I_D = 0.3\text{A}$, $T_C = 90^\circ\text{C}$, $t_p = 5\text{s}$	240			W

Source-Drain Diode

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values			
		Min.	Typ.	Max.	
I_S	$V_{GS} = 0\text{V}$			22	A
I_{SM}	Repetitive, Pulse Width Limited by T_{JM}			50	A
V_{SD}	$I_F = I_S$, $V_{GS} = 0\text{V}$, Note 1			1.5	V
t_{rr}	$I_F = I_S$, $-di/dt = 100\text{A}/\mu\text{s}$, $V_R = 100\text{V}$, $V_{GS} = 0\text{V}$		1000		ns

Note 1. Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.

SOT-227B (IXTN) Outline



(M4 screws (4x) supplied)

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.240	1.255	31.50	31.88
B	.307	.323	7.80	8.20
C	.161	.169	4.09	4.29
D	.161	.169	4.09	4.29
E	.161	.169	4.09	4.29
F	.587	.595	14.91	15.11
G	1.186	1.193	30.12	30.30
H	1.496	1.505	38.00	38.23
J	.460	.481	11.68	12.22
K	.351	.378	8.92	9.60
L	.030	.033	0.76	0.84
M	.496	.506	12.60	12.85
N	.990	1.001	25.15	25.42
O	.078	.084	1.98	2.13
P	.195	.235	4.95	5.97
Q	1.045	1.059	26.54	26.90
R	.155	.174	3.94	4.42
S	.186	.191	4.72	4.85
T	.968	.987	24.59	25.07
U	-.002	.004	-0.05	0.1

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338 B2
4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

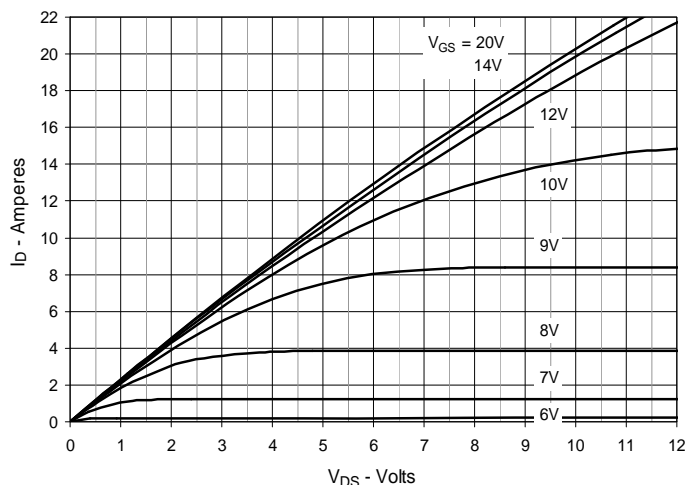


Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

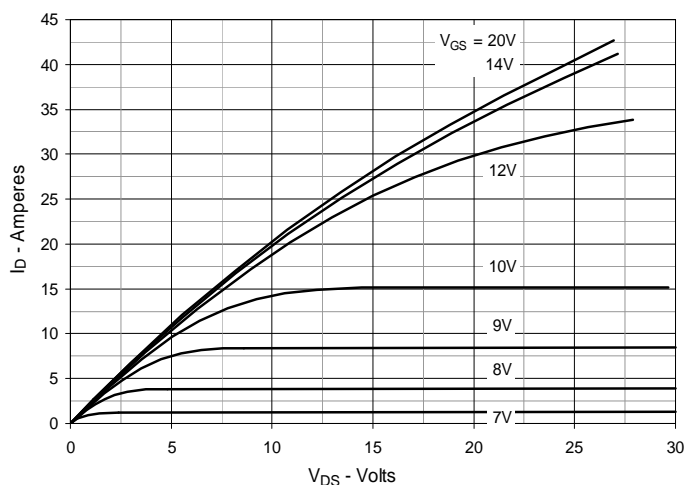


Fig. 3. Output Characteristics @ $T_J = 125^\circ\text{C}$

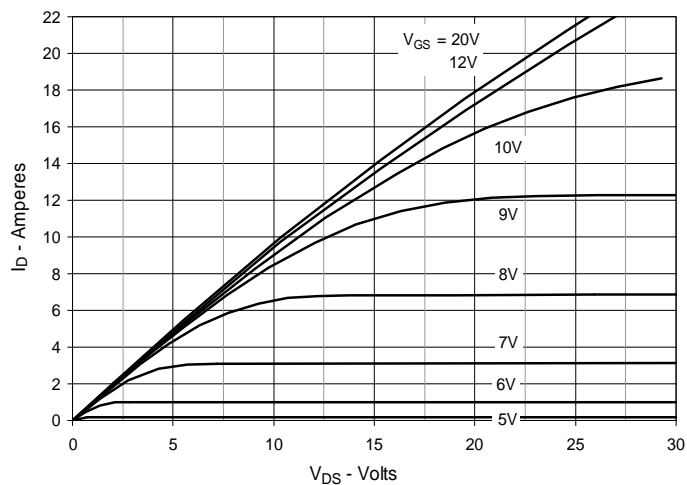


Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 11\text{A}$ Value vs. Junction Temperature

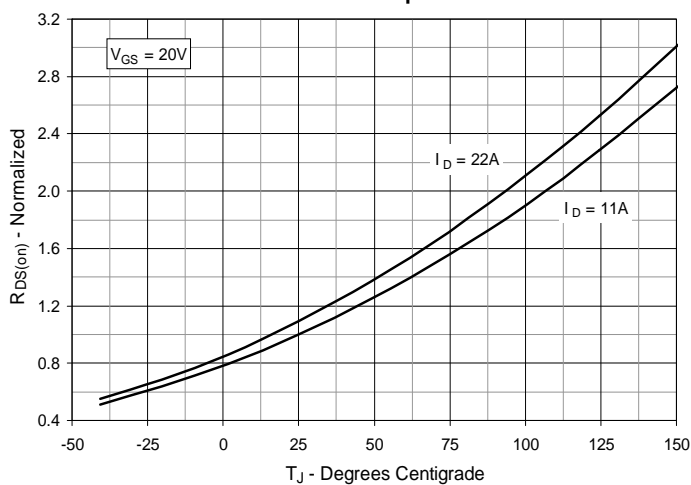


Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 11\text{A}$ Value vs. Drain Current

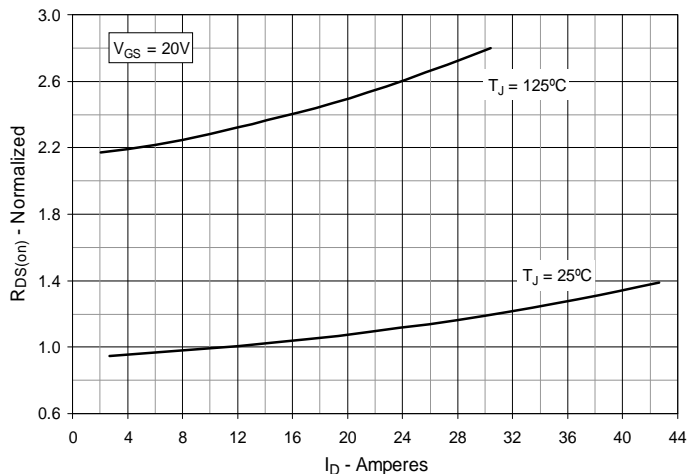


Fig. 6. Maximum Drain Current vs. Case Temperature

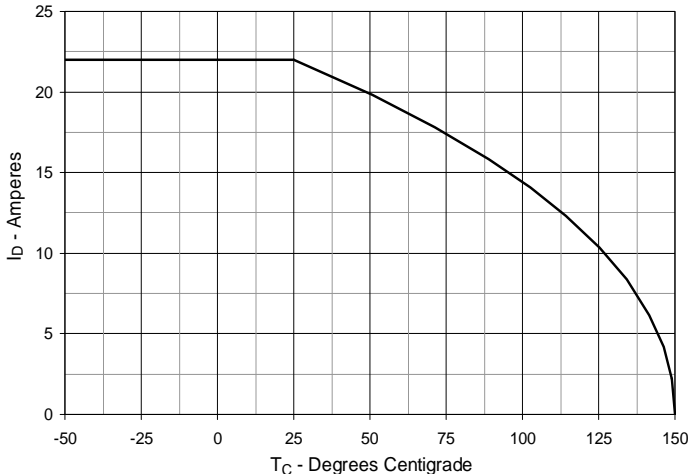


Fig. 7. Input Admittance

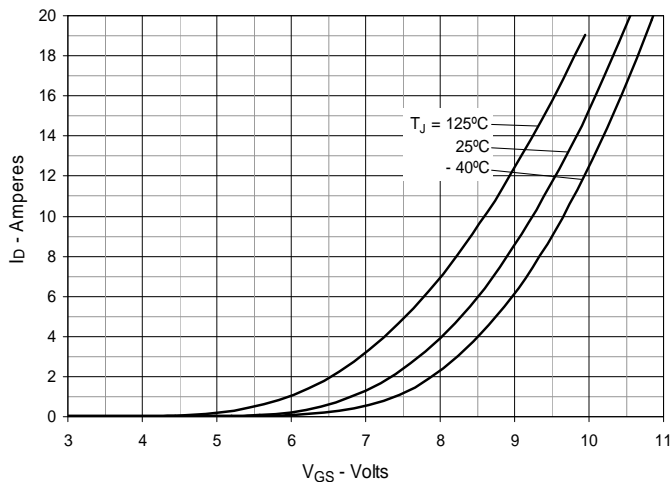


Fig. 8. Transconductance

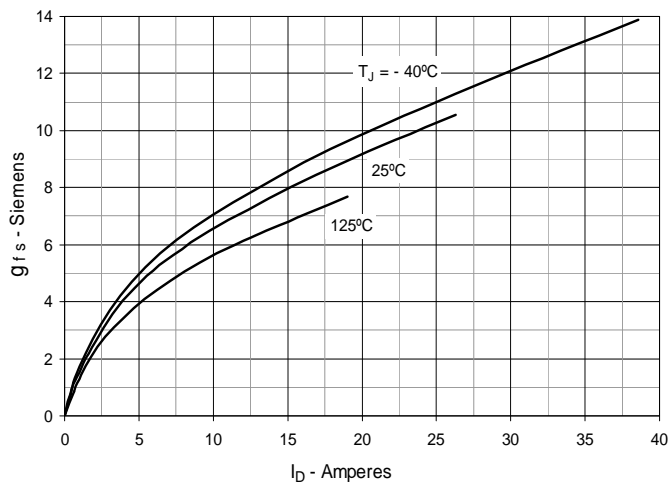


Fig. 9. Forward Voltage Drop of Intrinsic Diode

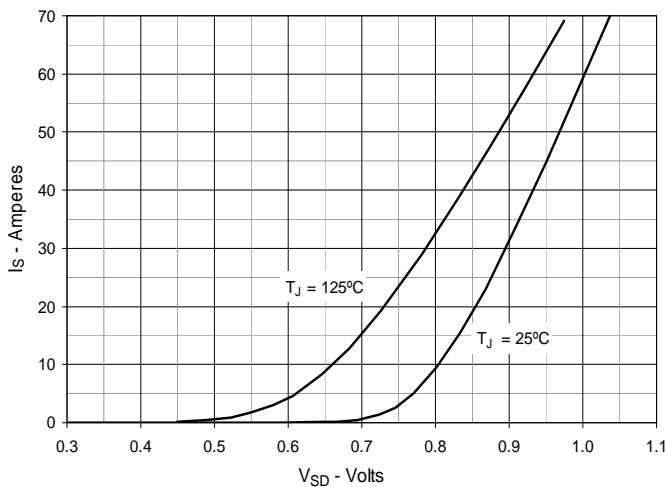


Fig. 10. Gate Charge

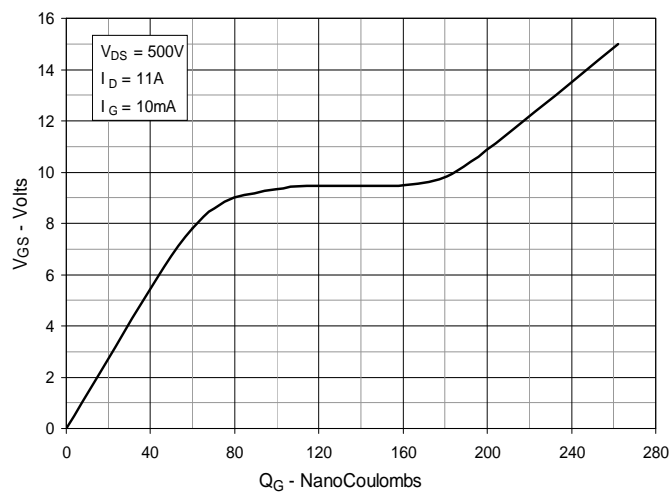


Fig. 11. Capacitance

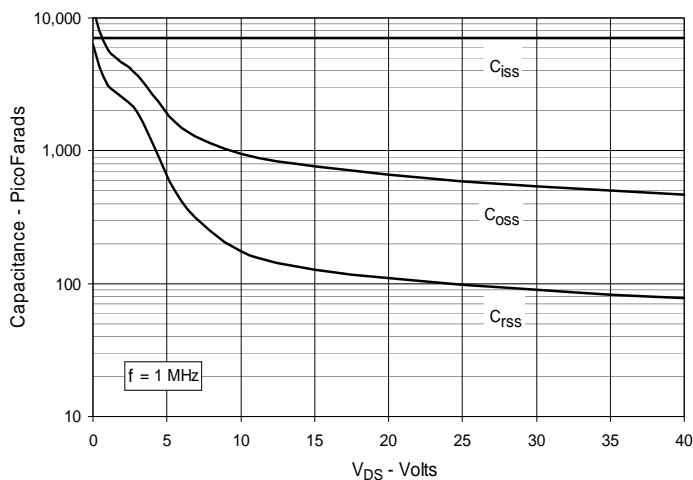


Fig. 12. Maximum Transient Thermal Impedance

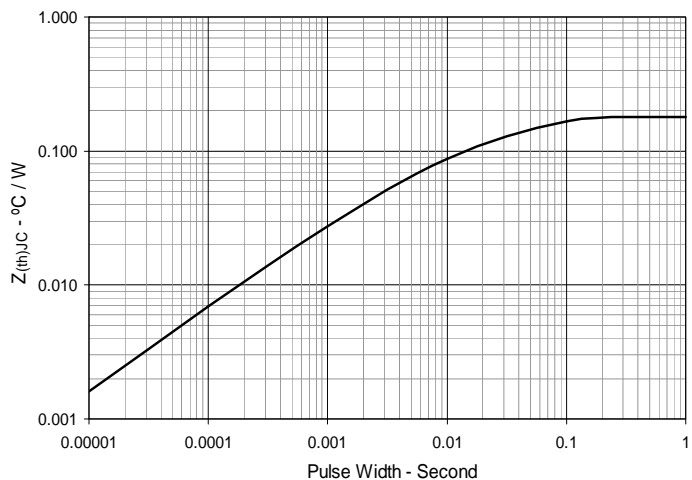


Fig. 13. Forward-Bias Safe Operating Area
 @ $T_C = 25^\circ\text{C}$

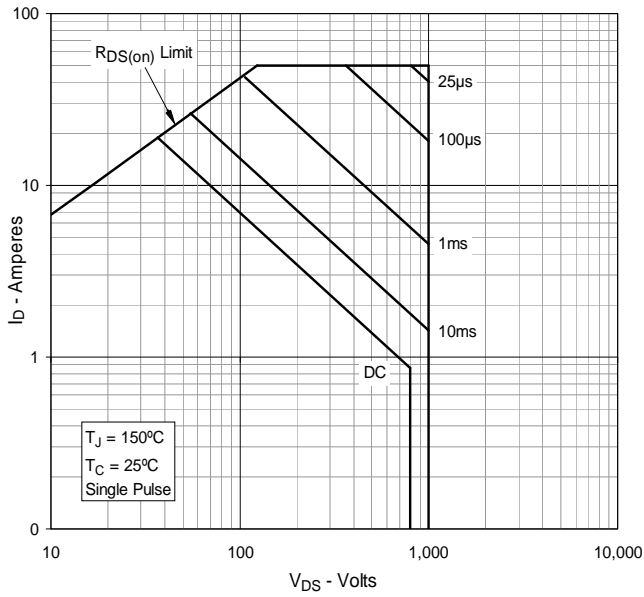


Fig. 14. Forward-Bias Safe Operating Area
 @ $T_C = 90^\circ\text{C}$

